Ref #	Hits	Search Query	DBs	Default Operator	Plurais	Time Stamp
S1	864268	transistor	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:07
S3	173500	(silicon near nitride) ("Si.sub.3N.sub.2") ("Si.sub.2N.sub.3")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:09
S2	572725	(gate with insulating with (film layer)) (insulating with (film layer)) (gate with dielectric) (gate with insulator)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:09
S8	188	S5 same S6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:10
S6	266964	fluorine	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:10
S5 ·	8761	S3 with S4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:10
S4	303361	amorphous .	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:10
S 7	111	S5 with S6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:12
S12	1196	S11 and gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/06/14 11:14
S11	¹ 1456	S1 and S10	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:14
S10	3615	S2 with S6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:14

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S9	6212	S2 same S6	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:14
S13	4831253	concentration amount	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 11:22
S14	936	S12 and S13	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/14 12:41
S19	269019	fluorine	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:10
S18	175113	(silicon near nitride) ("Si.sub.3N.sub.2") ("Si.sub.2N.sub.3")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:10
S17	1116772	gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:10
S16	118149	(thin with film with transistor) TFT	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:10
S22	8839	S21 with S18	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:11
S21	305696	amorphous	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:11
S20	2272	((gate with insulat\$3) S18) with S19	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:11
S24	276	S16 and S23	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:12

S23	667	((gate with insulat\$3) S22) with S19	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/16 16:12
S25	15887	Renesas.as.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/19 13:07
S26	406	fluorine near ion near implant\$5	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/19 13:08
S27	5	S25 and S26	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/19 13:14
S28	2	("20020079547").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 13:16
S30	2	("6159872").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 13:18
S29	2	("20050142821").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 13:18
S15	2	("5837614").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 15:50
S33	306154	amorphous	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/19 15:54
S31	6437	((silicon near2 nitride) SiN) near4 (gate with (insulat\$3 dielectric))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/19 15:54
S34	264	(((silicon near2 nitride) SiN) near2 S33) with (gate with (insulat\$3 dielectric))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:32

L3	208	1 and L2	US-PGPUB;	OR	ON	2007/07/20 08:34
		·	USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB			
L2	175466	(silicon near nitride) ("Si.sub.3N.sub.2") ("Si.sub.2N.sub.3")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:34
L1	422	(257/E21.276).CCLS.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/20 08:34
L7	616	fluorinated with 2	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:41
L5	3757	2 same (fluorine (F near atoms))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:41
L4	171	3 and (fluorine (F near atoms))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:41
L9	62	7 same gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:42
L8	1794	2 with (fluorine (F near atoms))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/20 08:42